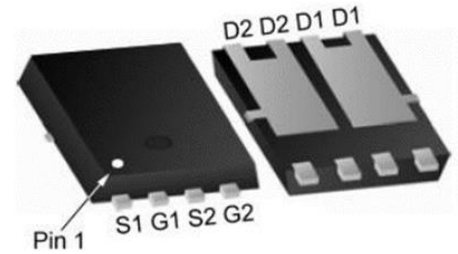


Description

The MOSFET provide excellent $R_{DS(on)}$ with low gate charge. This device is suitable for use as a wide variety of applications.

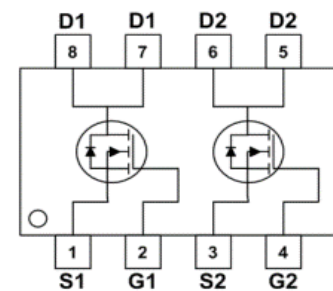
MOSFET Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
30	<15@ $V_{GS}=10V$	12
	<20@ $V_{GS}=4.5V$	



PDFN3.3*3.3-8L

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram

Absolute maximum ratings @ $T_A=25^\circ C$ (unless otherwise specified)

Parameter	Symbol	Typ	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current- Continuou	I_D	12	A
Drain Current- Continuous($T_C=70^\circ C$)	I_D	9	A
Pulse Drain Curren	I_{DM}	48	A
Maximum Power Dissipation	P_D	1.7	W
Operating Junction and Storage Temperature Range ⁽¹⁾	T_J, T_{STG}	-55 to 150	$^\circ C$
Thermal Characteristic			
Parameter	Symbol	Typ	Units
Thermal Resistance, Junction to Ambient ⁽²⁾	$R_{\theta JA}$	75	$^\circ C/W$

Electrical characteristics per line @25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics⁽³⁾						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.8	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=8A$	11	12	15	m Ω
		$V_{GS}=4.5V, I_D=6A$	14	15.5	20	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=8A$	-	24	-	S
Dynamic Characteristics⁽⁴⁾						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V, F=1.0MHz$	-	980	-	PF
Output Capacitance	C_{oss}		-	131	-	PF
Reverse Transfer Capacitance	C_{rss}		-	109	-	PF
Switching Characteristics⁽⁴⁾						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=8A,$ $V_{GEN}=4.5V, R_G=1.5\Omega$	-	4.2	-	nS
Turn-on Rise Time	t_r		-	8.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	31	-	nS
Turn-Off Fall Time	t_f		-	4	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=8A,$ $V_{GS}=4.5V$	-	9.63	-	nC
Gate-Source Charge	Q_{gs}		-	3.88	-	nC
Gate-Drain Charge	Q_{gd}		-	3.44	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ⁽³⁾	V_{SD}	$V_{GS}=0V, I_S=20A$	-	-	1	V
Diode Forward Current ⁽²⁾	I_S	-	-	-	9	A

Notes 1. Repetitive Rating: Pulse with limited by maximum junction temperature.

Notes 2. Surface mounted on FR4 board, $t \leq 10sec$.

Notes 3. Pulse test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Notes 4. Guaranteed by design, not subject to production.

Typical Characteristics

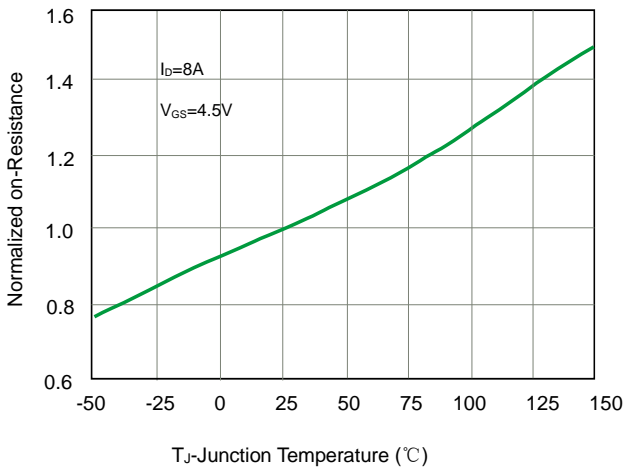


Fig.1 Rdson-Junction Temperature

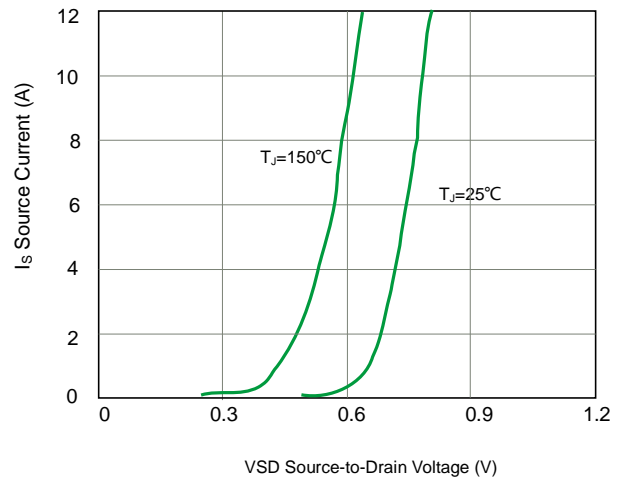


Fig.2 Transfer Characteristics

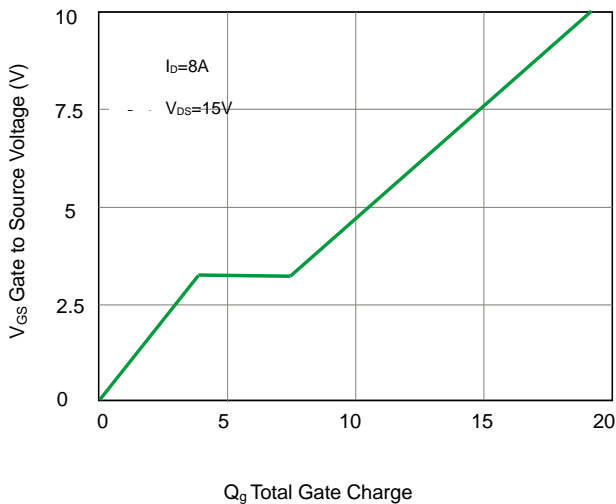


Fig.3 Gate Charge

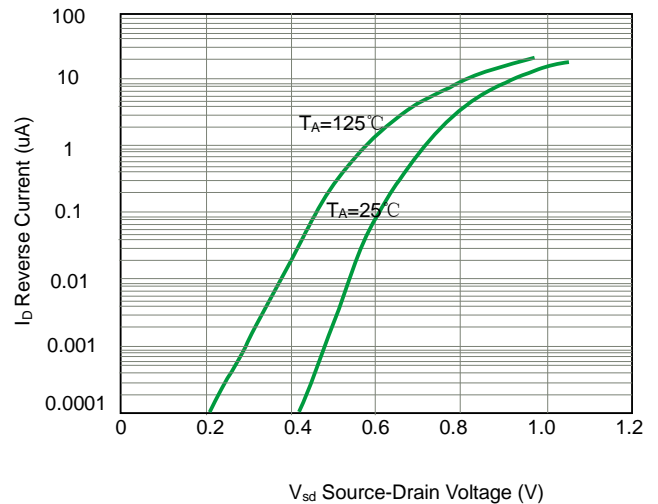


Fig.4 Source-Drain Diode Forward

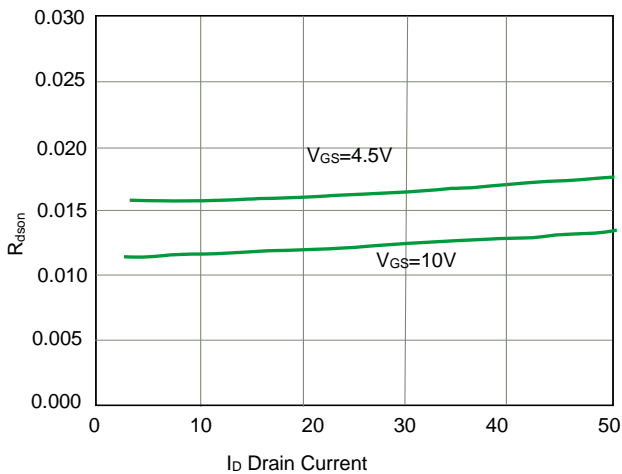


Fig.5 Rdson vs ID

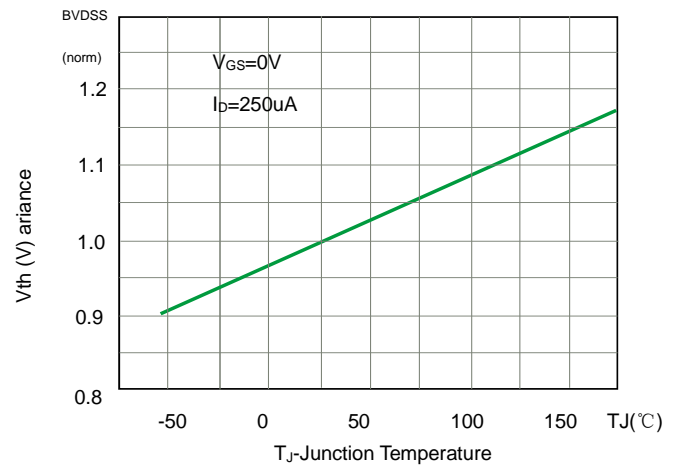


Fig.6 BV_{DSS} VS Junction Temperature

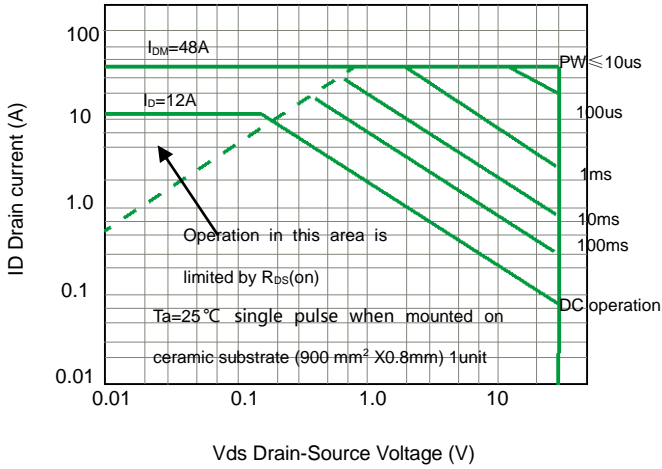


Fig.7 Safe Operation Area

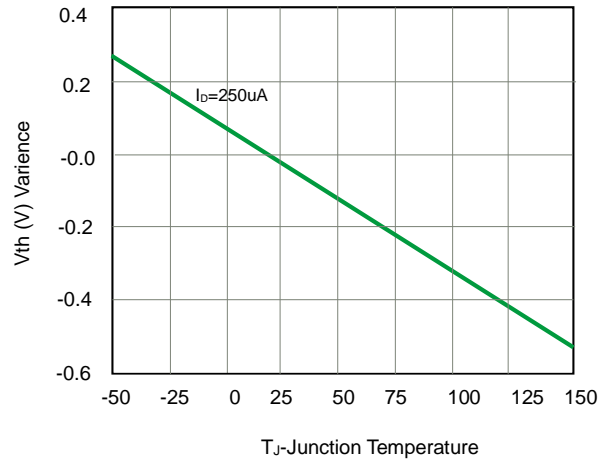


Fig.8 $V_{GS(th)}$ vs Junction Temperature

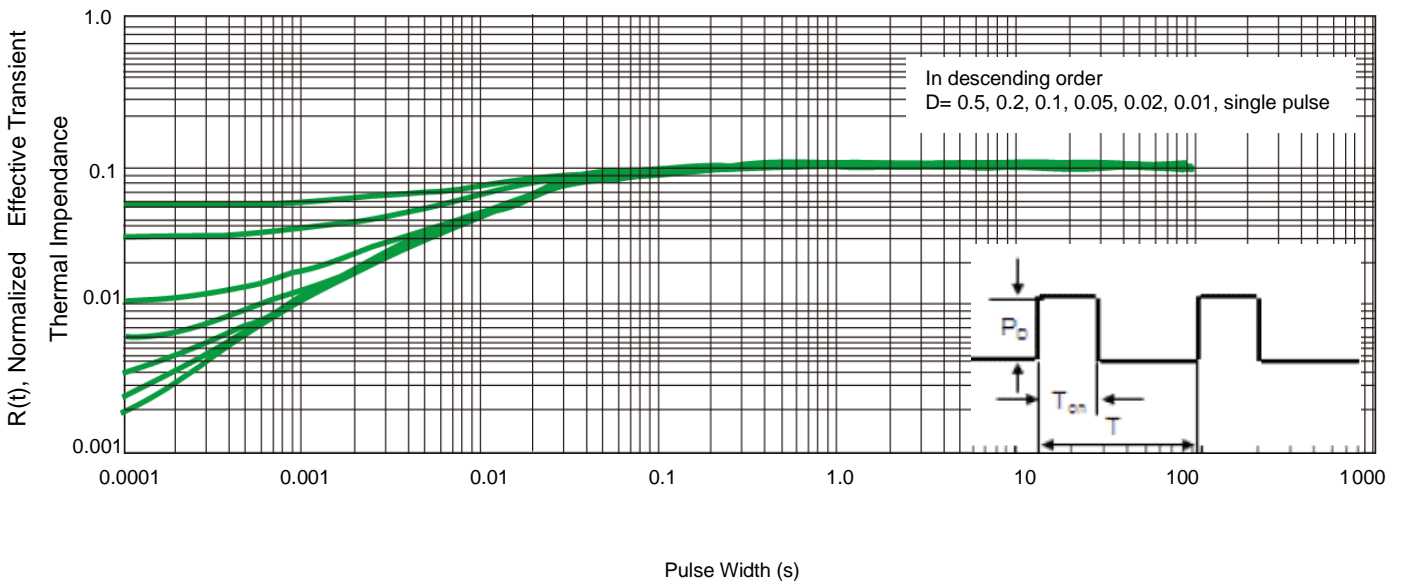
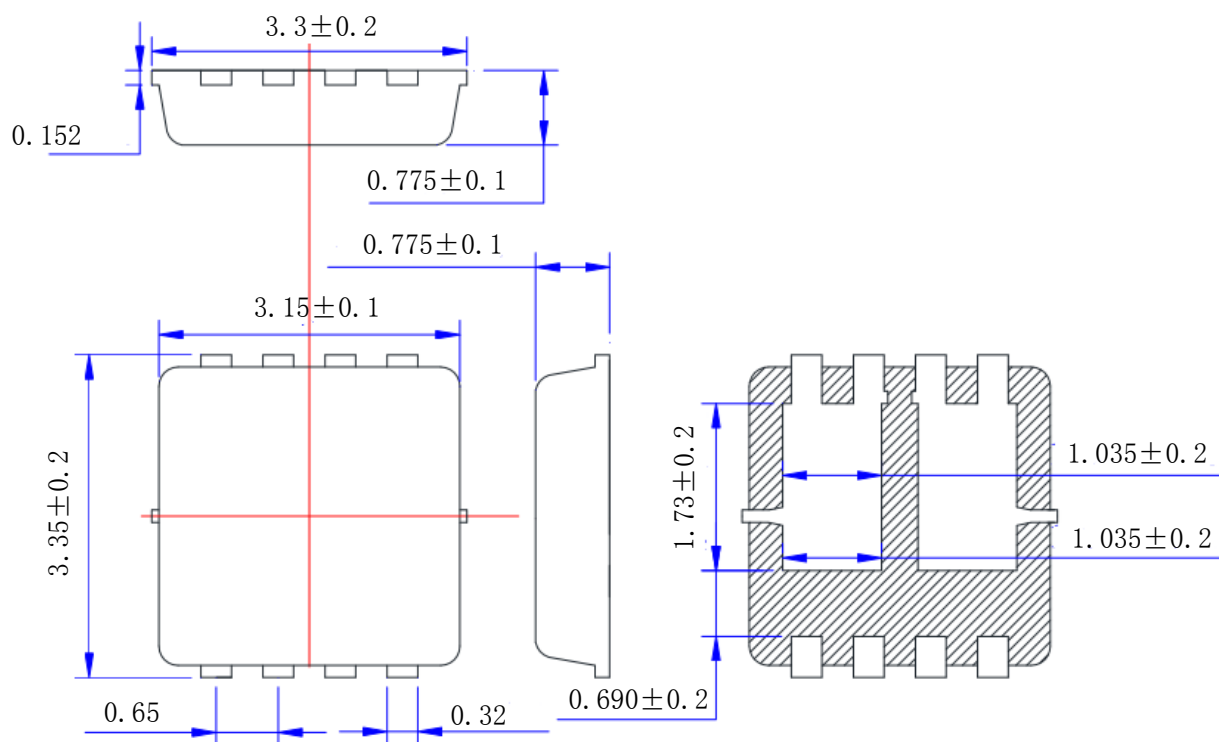


Figure 9. Normalized Maximum Transient Thermal Impedance

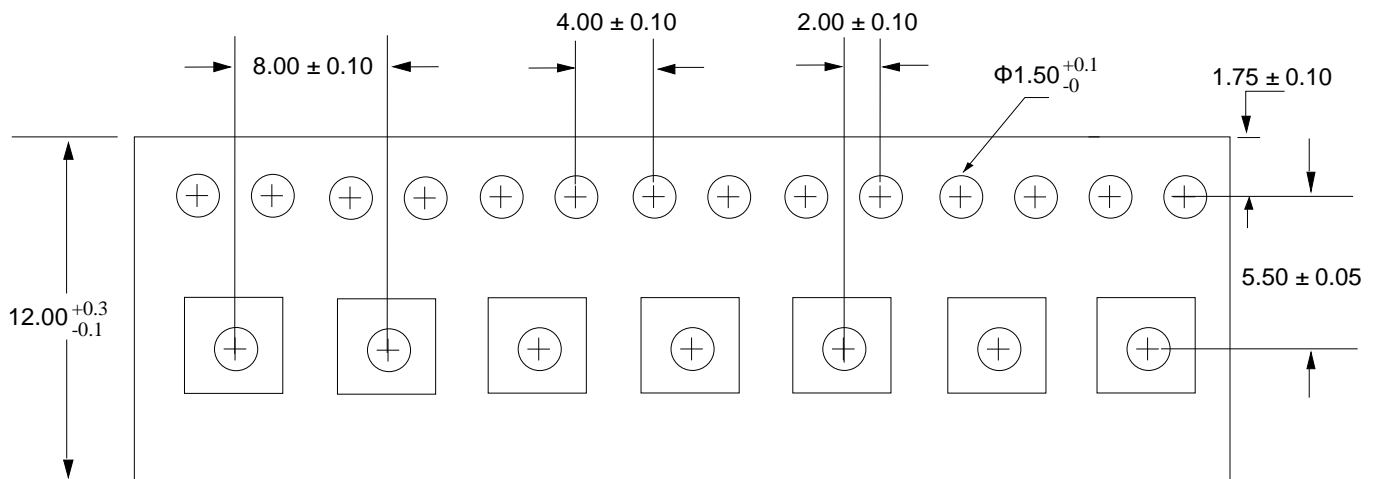
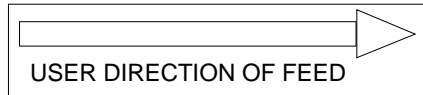
Product dimension (PDFN3.3*3.3-8L)



Ordering information


Device	Package	Reel	MPQ
PDNM8PN30V12	PDFN 3.3*3.3-8L (Pb-Free)	13"	5000 / Tape & Reel

Load with information



Unit: mm

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